

AllnGaP LED DICE

Part NO.: AOC-S12RxM-65 Series

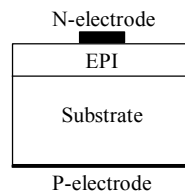
Features

- Red color emission
- Excellent performance and high efficiency
- Great reliability even in harsh environment
- Mirror reflector to increase efficiency

Description

AOC-S12RxM-65 series is a red color emitting AllnGaP LED grown by MOCVD technique. Its structure enables enhanced quantum efficiency; the mirror reflector greatly increases the light extraction efficiency and therefore a greater light intensity. This device is designed for use in high ambient light condition.

Chip Dimensions



Chip Size : 290 μ m \times 290 μ m \pm 25 μ m
 Bonding Pad : ϕ 105 μ m \pm 10 μ m
 Chip Thickness : 165 μ m \pm 25 μ m

Electrical and Optics Characteristics

Measuring Item	Symbol	Condition	Min	Typ.	Max	Unit
Forward Voltage	V _F	I _F =20mA	1.75	-	2.40	V
Reverse Current	I _R	V _R =5V	-	-	1.0	μ A
Dominant Wavelength	λ_d	I _F =20mA	616	-	630	nm
Max. Junction Temperature	T _{max}	-	\leq 120			$^{\circ}$ C
Max. DC forward current	I _F	T _a = 25 $^{\circ}$ C	\leq 50			mA
Max. pulse forward current (Pulse width 0.1 msec, frequency=1 kHz.)	I _{fm}	T _a = 25 $^{\circ}$ C	\leq 100			mA
Storage temperature	T _{stg}	Chip on tape	0 ~ 40			$^{\circ}$ C
		Only chip	-40 ~ 80			

Available Dominate Wavelength and Iv Matrix

Part No.	Wavelength Range	\geq 460 mcd	\geq 520 mcd	\geq 600 mcd	\geq 700 mcd	\geq 800 mcd
S12RSM-65	616 ~ 625 nm	-	Y52	Y60	-	-
S12RMM-65	620 ~ 630 nm	Y46	Y52	Y60	-	-

Note:

1. All measurements are done with AOC's standard testing equipment.
2. Luminance intensity is measured on bare chip.
3. Above contents are subject to change without notice.
4. Special requests are also welcome, please contact AOC's sale representative for any request.
5. Characteristics curves are measured within TO-46 package.

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